ISSN 0022-0248

JOURNAL OF CRYSTAL GROWTH

VOLUME 101

MASTER INDEX

Volumes 101–110

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North-Holland

JCRGAE 101–110 (MI) 1015–1100 (1991)

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PUBLISHED MONTHLY

Library of Congress Catalog Card Number 68-26537

PRINTED IN THE NETHERLANDS

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North-Holland

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Proceedings of the 1st International Conference, Auburn, AL, USA, 17-22 August, 1991
edited by **Y. Tzeng, M. Yoshikawa, M. Murakawa** *and* **A. Feldman**

Materials Science Monographs Volume 73
1991 900 pages; US $ 243.00 / Dfl. 425.00; ISBN 0-444-89162-5

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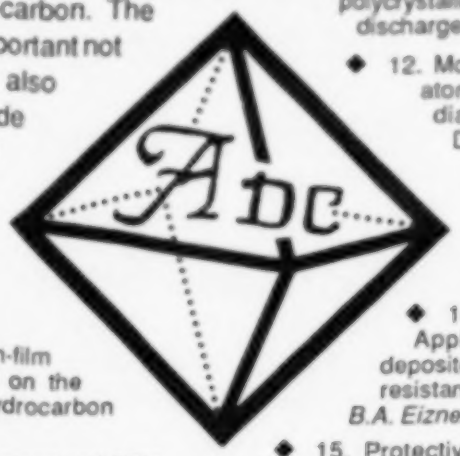

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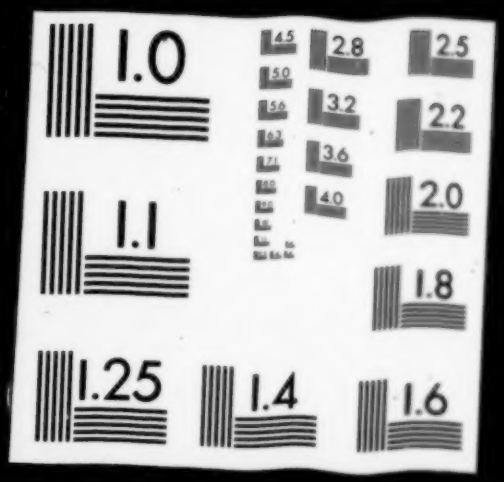
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